

SANYO Semiconductors DATA SHEET

SPA13003 (13003 series)

NPN Triple Diffused Planar Silicon Transistor

Switching Regulator Applications

Features

- · High breakdown voltage.
- · High-speed switching.
- · Wide ASO.
- · Adoption of MBIT process.

Specifications

Absolute Maximum Ratings at Ta=25°C

| Parameter | Symbol | Conditions | Ratings | Unit |
|------------------------------|--------|--------------------------|-------------|------|
| Collector-to-Base Voltage | VCBO | | 700 | V |
| Collector-to-Emitter Voltage | VCES | | 700 | V |
| Collector-to-Emitter Voltage | VCEO | | 400 | V |
| Emitter-to-Base Voltage | VEBO | | 8 | V |
| Collector Current | IC | | 1 | Α |
| Collector Current (Pulse) | ICP | PW≤300μs, duty cycle≤10% | 2 | Α |
| Base Current | IB | | 0.5 | Α |
| Collector Dissipation | PC | | 0.6 | W |
| Junction Temperature | Tj | | 150 | °C |
| Storage Temperature | Tstg | | -55 to +150 | °C |

Electrical Characteristics at Ta=25°C

| Parameter | Symbol | Conditions | Ratings | | | Unit |
|--------------------------|--------|---|---------|-----|-----|------|
| | | | min | typ | max | Unit |
| Collector Cutoff Current | ICBO | V _{CB} =400V, I _E =0A | | | 10 | μΑ |
| Emitter Cutoff Current | IEBO | V _{EB} =5V, I _C =0A | | | 10 | μΑ |
| DC Current Gain | hFE1 | V _{CE} =5V, I _C =0.1A | 15 | | 35 | |
| | hFE2 | V _{CE} =5V, I _C =0.5A | 5 | | | |
| | hFE3 | V _{CE} =5V, I _C =1mA | 7 | | | |

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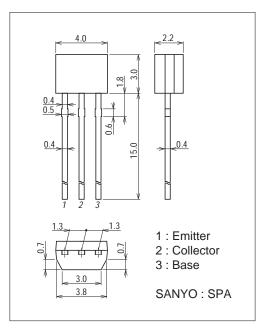
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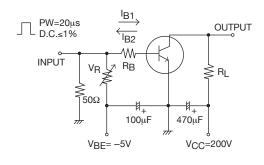
| Parameter | Symbol | Conditions | Ratings | | | Unit |
|---|-----------------------|---|---------|-----|-----|------|
| | | | min | typ | max | Unit |
| Gain-Bandwidth Product | fŢ | V _{CE} =10V, I _C =0.1A | | 20 | | MHz |
| Output Capacitance | Cob | V _{CB} =10V, f=1MHz | | 10 | | pF |
| Collector-to-Emitter Saturation Voltage | VCE(sat) | IC=0.5A, IB=0.1A | | | 0.8 | V |
| Base-to-Emitter Saturation Voltage | V _{BE} (sat) | I _C =0.5A, I _B =0.1A | | | 0.5 | V |
| Collector-to-Base Breakdown Voltage | V(BR)CBO | I _C =1mA, I _E =0A | 700 | | | V |
| Collector-to-Emitter Breakdown Voltage | V(BR)CES | I _C =100μA, R _{BE} =0Ω | 700 | | | V |
| Collector-to-Emitter Breakdown Voltage | V(BR)CEO | IC=5mA, RBE=∞ | 400 | | | V |
| Emitter-to-Base Breakdown Voltage | V(BR)EBO | I _E =1mA, I _C =0A | 8 | | | V |
| Turn-On Time | ton | I _C =0.5A, I _B 1=0.05A, I _B 2=-0.5A, R _L =400Ω, V _{CC} =200V | | | 1.0 | μS |
| Storage Time | t _{stg} | I _C =0.5A, I _B 1=0.05A, I _B 2=-0.5A, R _L =400Ω, V _{CC} =200V | | | 1.0 | μS |
| Fall Time | tf | IC=0.5A, IB1=0.05A, IB2=-0.5A, RL=400Ω, VCC=200V | | | 0.3 | μS |

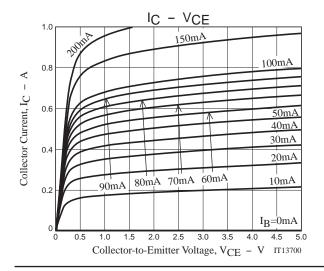
Package Dimensions

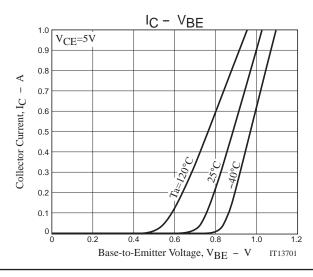
unit : mm (typ) 7524-004

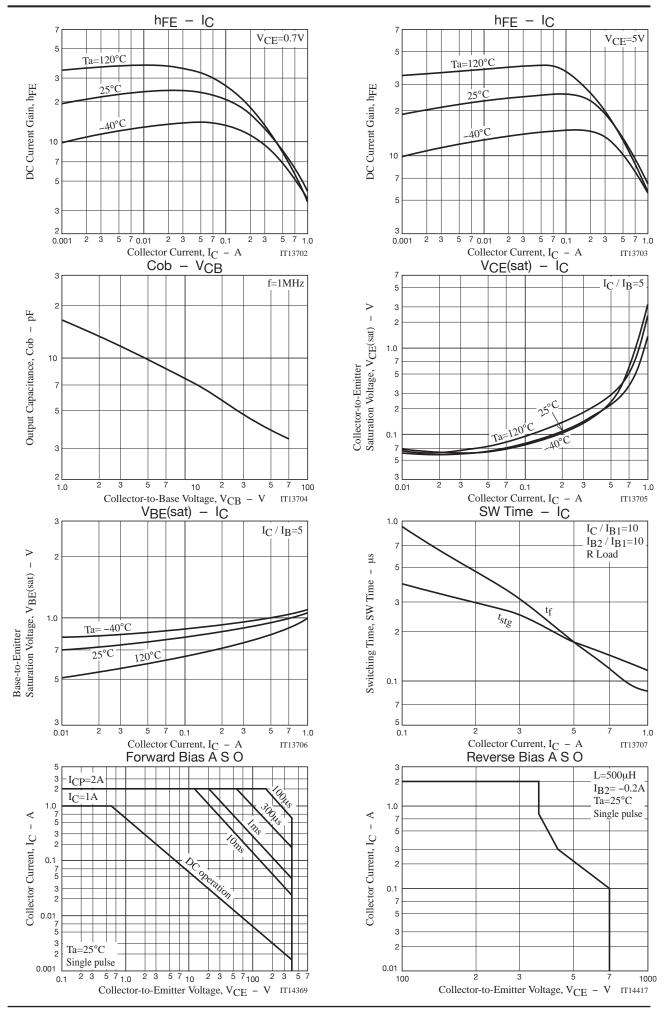


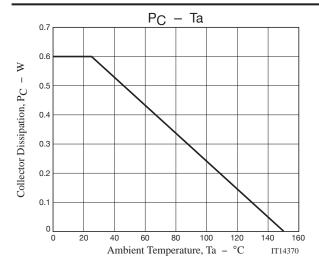
Switching Time Test Circuit











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